

40V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

- BV_{CEO} > -40V
- I_C = -2A high Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ I_C = -1A.
- R_{CE(SAT)} = 90mΩ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary NPN Type: ZXTN4240F
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

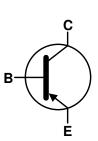
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight 0.008 grams (Approximate)

Application

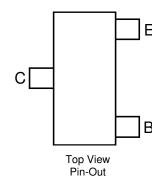
- Gate Driving MOSFETs and IGBTs
- Load Switch
- DC-DC Converters
- Battery Charging







Device Symbol



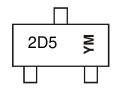
Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP5240F-7	2D5	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2018) M = Month (ex: 9 = September)

Date Code Kev

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Year	2018	2019	2020	2021	2022	2023	202	24 2	025	2026	2027	2028
Code	F	G	Н		J	K	L		М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Collector Current	I _{CM}	-3	Α
Continuous Collector Current	I _C	-2	А
Base Current	I _B	-300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	730	mW
Power Dissipation (Note 6)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	R _{0JA}	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	$R_{\theta JL}$	75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

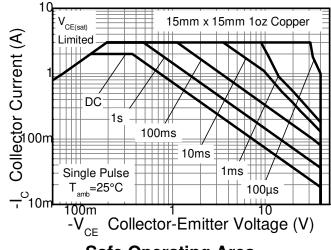
Notes:

- 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

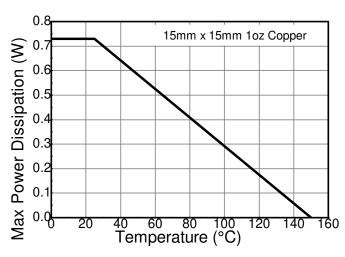
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



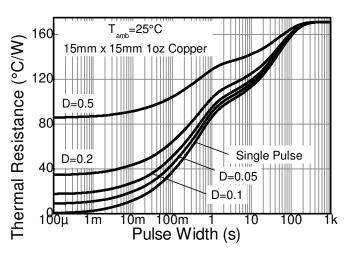
Thermal Characteristics and Derating Information



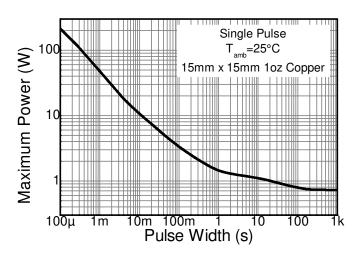




Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

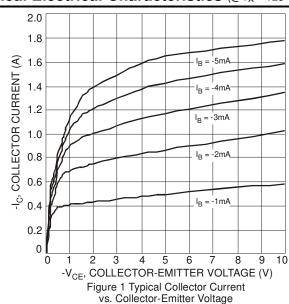


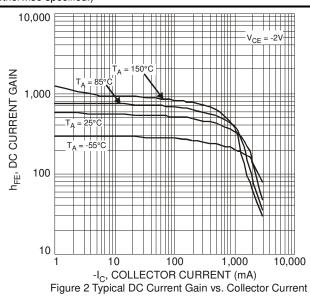
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-40	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	_	_	V	$I_E = -100\mu A$
Collector-Base Cutoff Current	_	_	_	-100	nA	$V_{CB} = -30V, I_{E} = 0$
Collector-base Guton Gurrent	I _{CBO}	_	_	-50	μΑ	$V_{CB} = -30V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -4V, I _C = 0
ON CHARACTERISTICS (Note 9)						
		300		_		$V_{CE} = -2V, I_{C} = -0.1A$
DC Current Gain	h	260		_		$V_{CE} = -2V, I_{C} = -0.5A$
Do Guilent Gain	h _{FE}	210	_		_	$V_{CE} = -2V, I_{C} = -1A$
		100				$V_{CE} = -2V$, $I_C = -2A$
		_		-100	mV	$I_C = -100 \text{mA}, I_B = -1 \text{mA}$
	V _{CE(SAT)}	_	-45	-110		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Voltage		_		-225		$I_C = -750 \text{mA}, I_B = -15 \text{mA}$
		_	_	-225		$I_C = -1A$, $I_B = -50mA$
		_	_	-350		I _C = -2A, I _B = -200mA
Equivalent On-Resistance	R _{CE(SAT)}	_	90	220	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_		-1.1	٧	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	_	_	-0.75	V	$V_{CE} = -2V, I_{C} = -100mA$
SMALL SIGNAL CHARACTERISTICS						
	t_{D}	_	21			
Switching times	t _R	_	22	_	ns	$V_{CC} = -10V$, $I_{C} = -500$ mA,
Owitining times	ts	_		113	$I_{B1} = I_{B2} = -50 \text{mA}$	
	t _F	_	23	_		
Transition Frequency	f⊤	100		_	MHz	V _{CE} = -10V, I _C = -100mA, f = 100MHz
Output Capacitance	C _{OB}			28	pF	V _{CB} = -10V, f = 1MHz

Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq 2\%.$

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







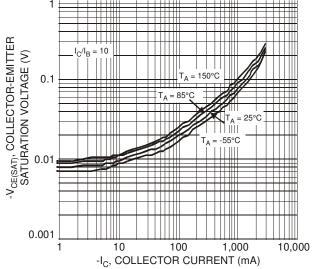


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

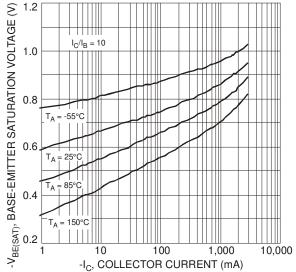


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

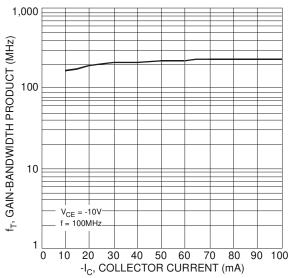


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

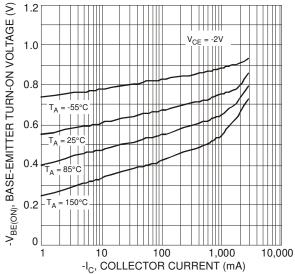


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

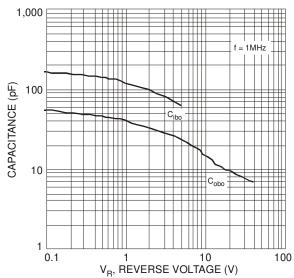


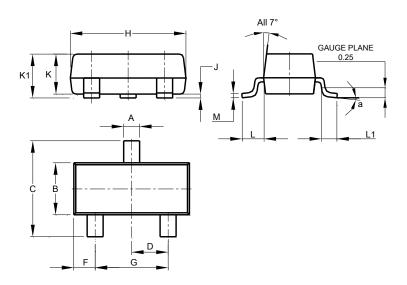
Figure 6 Typical Capacitance Characteristics



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

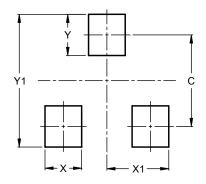


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
V1	2.0



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